

EEC 118 Lecture #16: Manufacturability

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Outline

- **Finish interconnect discussion**
- **Manufacturability: Rabaey G, H (Kang & Leblebici, 14)**

Design for Manufacturability

- **For class projects or university research, goal is a single working circuit or small number of prototypes**
 - Similar scale for industrial research projects
- **Production goal is usually thousands to 100s of millions of working (or at least marketable) parts**
 - Must evaluate circuit designs over a range of parameter variations to ensure correct functionality, performance
- **Design for Manufacturability or Statistical Circuit Design encompasses a variety of techniques**
 - Yield estimation and maximization, worst-case analysis, etc.

Circuit Parameter Variations

- **All circuit parameters vary some amount due to variations in process, lithography, or environment**
 - Geometric parameters: transistor W and L
 - Device parameters: V_T , t_{ox} , μ
 - Interconnect parameters: R , C
 - Operating conditions: V_{DD} , T
- **Variations occur both spatially and temporally**
 - Circuit-to-circuit on same die (spatial)
 - Die-to-die on same wafer (spatial)
 - Wafer-to-wafer in same fab (temporal)
- **Example: transistor width $W = W^0 + \Delta W$**

Designer controls
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_____↑
Random

Increasing
variation

CMOS Inverter Example

- **For both NMOS and PMOS:**

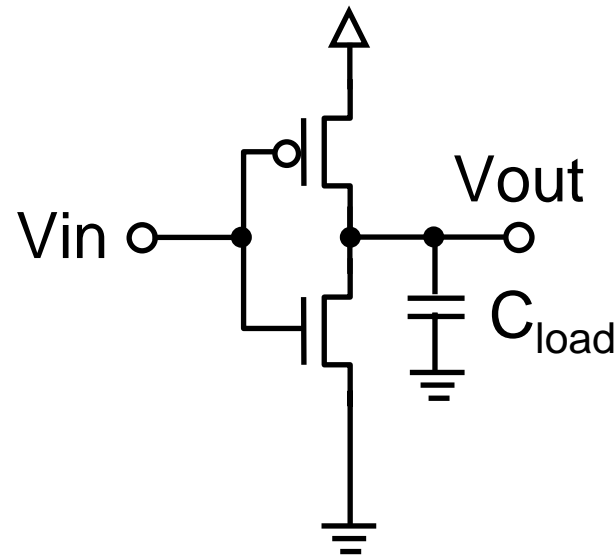
- $W = W^0 + \Delta W$
- $L = L^0 + \Delta L$
- $V_T = V_T^0 + \Delta V_T$
- $k' = k'^0 + \Delta k'$

- **For capacitor:**

- $C_{\text{load}} = C^0 + \Delta C$

- **For entire circuit:**

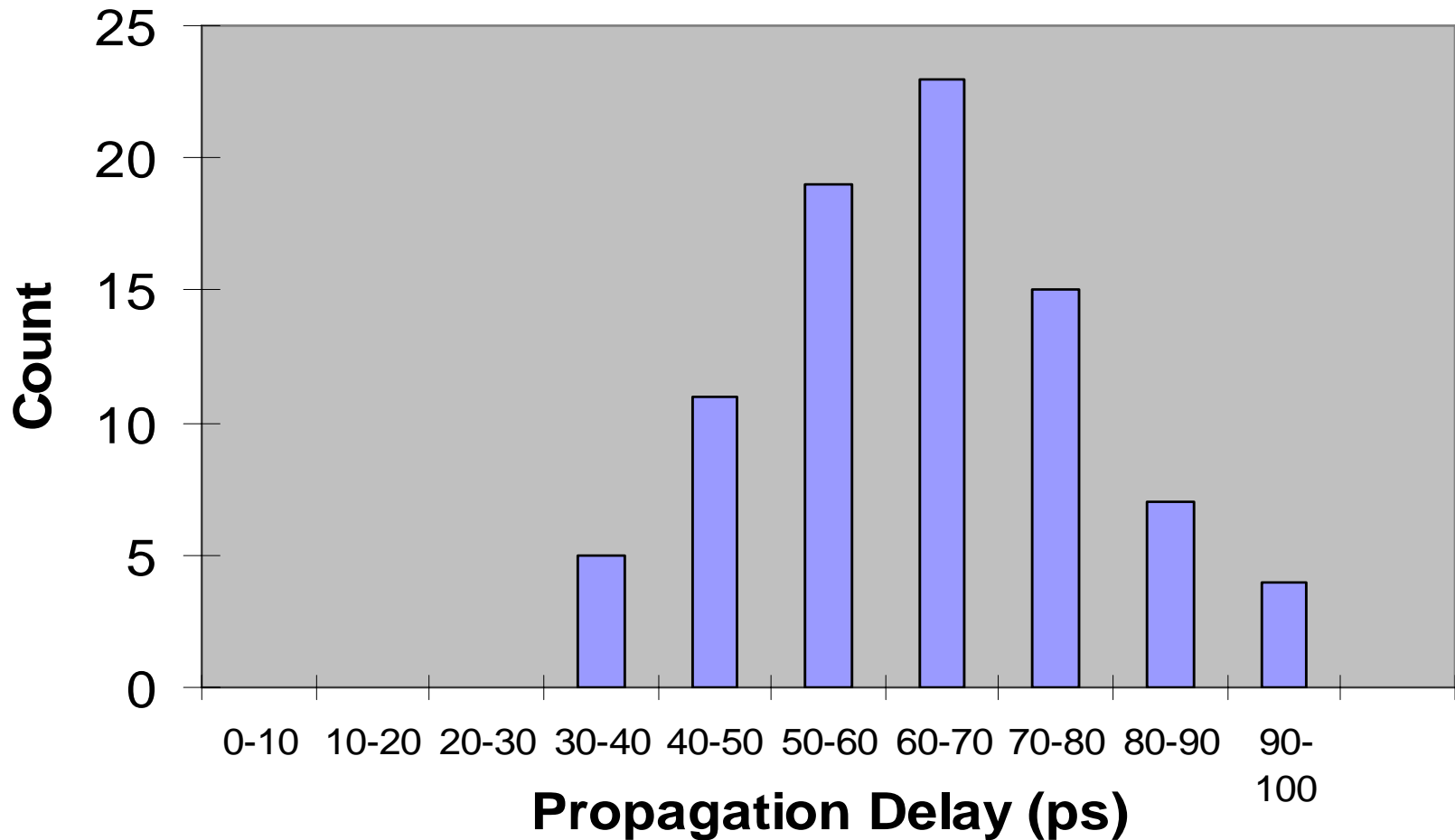
- $T = T^0 + \Delta T$
- $V_{DD} = V_{DD}^0 + \Delta V_{DD}$



- **All these parameters affect circuit performance!**

Performance Variation Example

Inverter Delay Histogram



- Delay variations with parameters, loading, V_{DD} , and T

Yield Estimation and Maximization

- **Parametric Yield:** ratio of total acceptable circuits to total manufactured circuits
 - Design for manufacturability aims to maximize yield (and \$\$)
- **Yield statistics are usually complicated since circuit performance is complex function of parameters**
- **Numerous methods for estimating and maximizing yield**
 - Response surface models (RSM): compact analytical model fit to circuit simulations using Design of Experiments
 - Direct Monte Carlo circuit simulations or the RSM can be used to estimate yields
 - Designer controlled parameters then adjusted to maximize yield estimates

Worst-Case Design 1

- **Given range of variations for process, voltage, temperature identify worst (best) cases for performance parameter of interest**
 - Process corner models from fab define limits of device performance
 - Labeled by NMOS-PMOS pairs, e.g. Typical NMOS-Typical PMOS (TT)
 - Usual additional corners: Fast NMOS-Fast PMOS (FF), Slow NMOS-Slow PMOS (SS), Fast NMOS-Slow PMOS (FS), Slow NMOS-Fast PMOS (SF)
 - Usual voltage corners: Nominal V_{DD} +/- 10%
 - Temperature range: 0 – 100 °C

Worst-Case Design 2

- **Identify worst (best) cases for performance parameter of interest**
- **Typical Speed Corner**
 - Typical NMOS-Typical PMOS (TT), nominal VDD, room temperature 27 °C
- **Slow Speed Corner**
 - Slow NMOS-Slow PMOS (SS), 0.9 x VDD, maximum temperature 100 °C
- **Fast Speed Corner**
 - Fast NMOS-Fast PMOS (FF), 1.1 x VDD, minimum temperature 0 °C

Summary

- **Design for manufacturability converts a prototype into a “real” design for large-scale production**
 - Statistical models of process, device and interconnect parameters, and operating conditions used to estimate and maximize yield (and profits)
 - Analysis is difficult because of complexity, usually numerical models and many simulations required
- **Variability trend is worsening as processes shrink**
 - For example, locations of individual dopant atoms can affect transistor performance
- **Statistical circuit design is becoming as important as performance and power!**

Next Topic: Future Directions & Final Review

- **Future directions in CMOS digital circuits**
- **Alternative logic technologies to CMOS**
- **Final exam review**